

German Gutierrez  
Application No.: 09/650,275  
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IN THE CLAIMS:

Please amend claim 1 as follows:

3uk  
BC1

1. (Amended) A die seal structure for a semiconductor die having a  
substrate comprising:  
an elongate region electrically isolated from the remainder of the substrate  
extending around a major portion of the periphery of the substrate and having a gap  
between ends of the elongate region along a minor portion of the periphery; and  
a conductive seal ring extending around the entire periphery of the die in  
direct contact with the die throughout said elongate region in direct contact with and said  
gap to provide a limited electrical connection between the ring and the substrate at said  
gap.

Please cancel claims 9-13. ~~14~~.

B3  
C1

14. (Amended) A die seal structure for a semiconductor die having a  
substrate of a first conductivity type, comprising:  
an elongate well region of a second conductivity type opposite from the  
first conductivity type extending around a major portion of the periphery of the substrate  
and having a gap between the ends of the elongate region along a minor portion of the  
periphery; and  
a conductive seal ring extending around the entire periphery of the die in  
direct contact with the die throughout said elongate well region and in said gap to provide  
a limited electrical connection between the ring and the substrate of said first  
conductivity type at said gap.

B3 C2

18. (Amended) A semiconductor device comprising:  
a. a die including a substrate;

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3                   b.       a die seal structure on the substrate, the structure comprising:  
4                               an elongate region electrically isolated from the remainder of the  
5 substrate extending around a major portion of the periphery of the substrate and having a  
6 gap between ends of the elongate region along a minor portion of the periphery; and  
7                   a conductive seal ring extending around the entire periphery of the die in  
8 direct contact with the die throughout said elongate region and in direct contact with said  
9 gap to provide a limited electrical connection between the ring and the substrate at said  
10 gap.

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